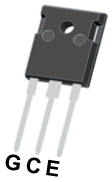
CGWT40N65F2KBT/CGPT40N65F2KBT

CGWT40N65F2KBT/CGPT40N65F2KBT

V_{CE}	Ic (Tc=100℃)	$V_{CE(sat)}$
650V	40A	1.62V

TO-247



TO-3P



DESCRIPTION

The CGWT40N65F2KBT/CGPT40N65F2KBT is used JSCJ's second generation IGBT technology, has advanced Trench and FS(Field Stop) Structure，it's with high application frequent, low Collector-Emitter Saturation Voltage and switching loss, can easy to use in parallel.

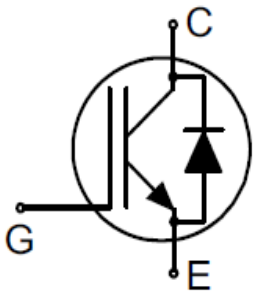
Features

- 650V breakdown Voltage
- Low Vce(sat) and positive temperature coefficient
- High speed switching，Low switching loss
- With fast and soft recovery freewheeling diode
- Good EMI behavior

Application

- UPS & PFC applications
- Solar Inverter
- Power Storage

EQUIVALENT CIRCUIT



MARKING

WT40N65F2KBT
▪XXXXX

WT40N65F2KBT/PT40N65F2KBT = Device code

Solid dot = Green molding compound device, if none, the normal device

XXXXX = Code

Order Code	Package	Marking	Parking
CGWT40N65F2KBT	TO-247	WT40N65F2KBT	Tube
CGPT40N65F2KBT	TO-3P	PT40N65F2KBT	Tube

感谢您的支持，如需要完整规格书，请联系：<igbt.list@jscj-elec.com>，谢谢!

Thank you for your support. If you need a complete datasheet, please contact:

<igbt.list@jscj-elec.com>. Thank you!